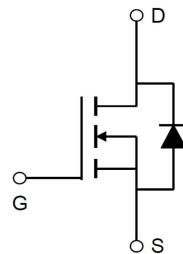
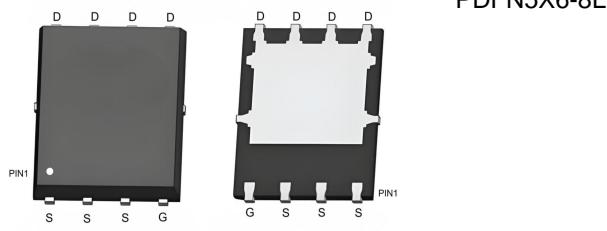


N-Channel 30V(D-S) MOSFET

Product summary			Features
V_{DS}	30	V	<ul style="list-style-type: none"> Advanced Trench Technology Low $R_{DS(ON)}$
$R_{DS(ON)}$ (at $V_{GS}=10V$) Typ.	6.6	$m\Omega$	Applications <ul style="list-style-type: none"> Load switching PWM Applications Power Management
$R_{DS(ON)}$ (at $V_{GS}=4.5V$) Typ.	11	$m\Omega$	
$I_D(T_c=25^\circ C)$	51	A	

Pin Configuration



Packing Information

Device	Package	Reel Size	Quantity(Min. Package)
ECAP51N03A	PDFN5X6-8L	13"	3000pcs

Absolute Maximum Ratings (at $T_A=25^\circ C$ Unless Otherwise Noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Continuous Drain Current	$T_c=25^\circ C$	A
		$T_c=100^\circ C$	A
I_{DM}	Pulse Drain Current Tested ^A	137	A
E_{AS}	Single Pulse Avalanche Energy ^B	39	mJ
P_D	Power Dissipation @ $T_c=25^\circ C$	48	W
T_J, T_{STG}	Junction and Storage Temperature Range	-55 to +150	°C

Thermal Characteristics

Symbol	Parameter	Typical	Units
$R_{\theta JC}$	Thermal Resistance-Junction to case max	2.6	°C/W

Electrical Characteristics (at $T_J = 25^\circ\text{C}$ Unless Otherwise Noted)

Symbol	Parameter	Condition	Min.	Typ.	Max.	Units
Static Parameters						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=250\mu\text{A}$	30	--	--	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{\text{DS}}=30\text{V}, V_{\text{GS}}=0\text{V}$	--	--	1	μA
I_{GSS}	Gate-Body Leakage Current	$V_{\text{DS}}=0\text{V}, V_{\text{GS}}=\pm 20\text{V}$	--	--	± 100	nA
$V_{\text{GS}(\text{th})}$	Gate Threshold Voltage	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=250\mu\text{A}$	1.0	1.5	2.5	V
$R_{\text{DS}(\text{ON})}$	Drain-Source On-State Resistance ^C	$V_{\text{GS}}=10\text{V}, I_{\text{D}}=20\text{A}$	--	6.6	8.6	$\text{m}\Omega$
		$V_{\text{GS}}=4.5\text{V}, I_{\text{D}}=15\text{A}$	--	11	15	$\text{m}\Omega$
V_{SD}	Diode Forward Voltage	$I_{\text{S}}=1\text{A}, V_{\text{GS}}=0\text{V}$	--	--	1.2	V
Dynamic Parameters ^D						
C_{iss}	Input Capacitance	$V_{\text{GS}}=0\text{V}, V_{\text{DS}}=15\text{V}$ $f=1\text{MHz}$	--	1116	--	pF
C_{oss}	Output Capacitance		--	187	--	pF
C_{rss}	Reverse Transfer Capacitance		--	152	--	pF
Q_g	Total Gate Charge	$V_{\text{DS}}=15\text{V}, I_{\text{D}}=15\text{A}$ $V_{\text{GS}}=10\text{V}$	--	13.3	--	nC
Q_{gs}	Gate-Source Charge		--	3.1	--	nC
Q_{gd}	Gate-Drain Charge		--	5	--	nC
$t_{\text{D(on)}}$	Turn-on Delay Time	$V_{\text{DS}}=15\text{V}$ $, R_{\text{GEN}}=3\Omega$ $I_{\text{D}}=30\text{A}$ $V_{\text{GS}}=10\text{V}$	--	15	--	ns
t_r	Turn-on Rise Time		--	19	--	ns
$t_{\text{D(off)}}$	Turn-off Delay Time		--	35	--	ns
t_f	Turn-off Fall Time		--	21	--	ns
t_{rr}	Reverse recovery time	$I_{\text{F}}=20\text{A}$ $di/dt=100 \text{ A/uS}$	--	14	--	ns
Q_{rr}	Reverse recovery charge		--	4.1	--	nC

A. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.

B. EAS condition: $T_J=25^\circ\text{C}$, $R_G=25\Omega$, $V_{\text{DD}}=15\text{V}$, $V_G=10\text{V}$, $L=0.5\text{mH}$, $I_{\text{AS}}=12.6\text{A}$.

C. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 0.5\%$.

D. Guaranteed by design, not subject to production testing.

Typical Characteristics

Figure 1: Output Characteristics

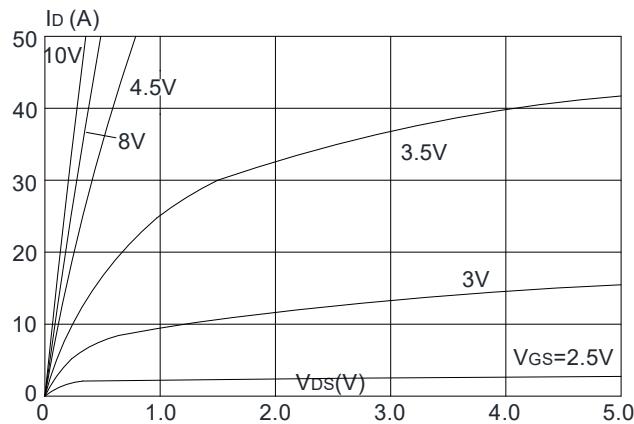


Figure 2: Typical Transfer Characteristics

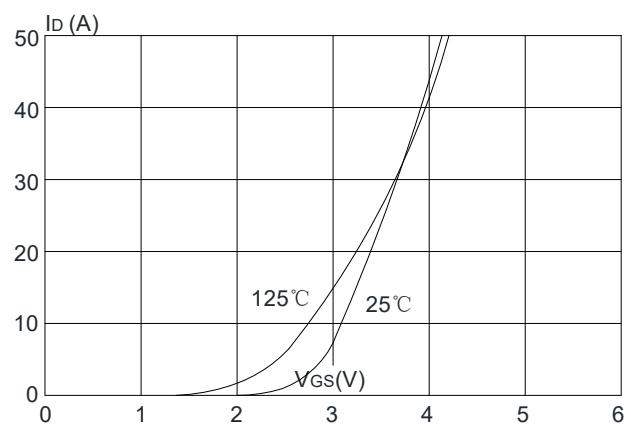


Figure 3: On-resistance vs. Drain Current

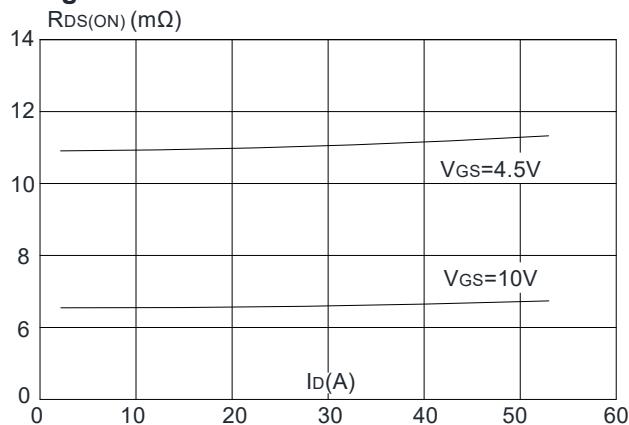


Figure 4: Body Diode Characteristics

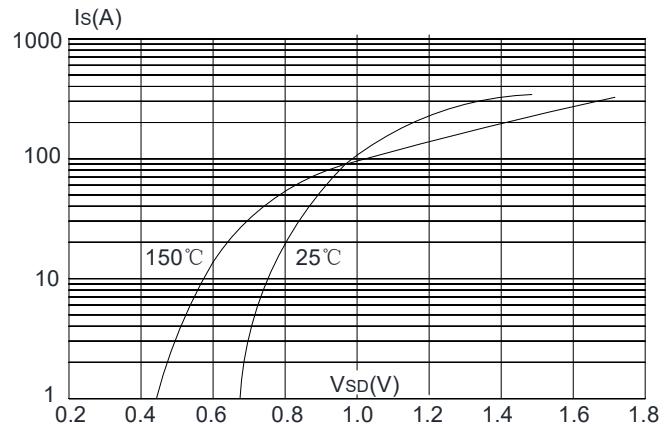


Figure 5: Gate Charge Characteristics

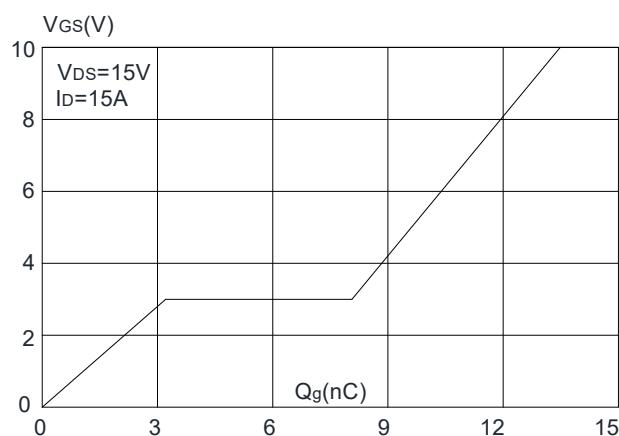
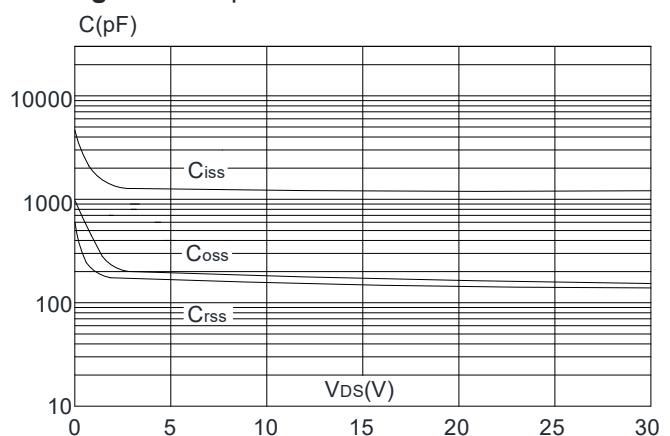


Figure 6: Capacitance Characteristics



Typical Characteristics

Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

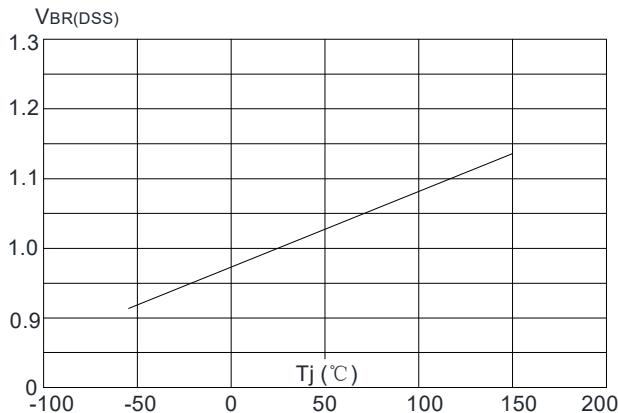


Figure 8: Normalized on Resistance vs. Junction Temperature

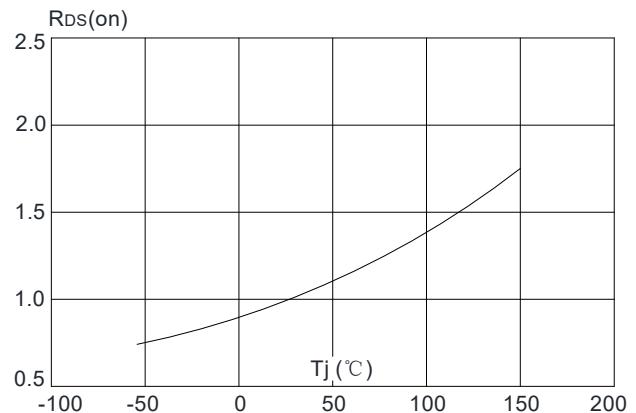


Figure 9: Maximum Safe Operating Area

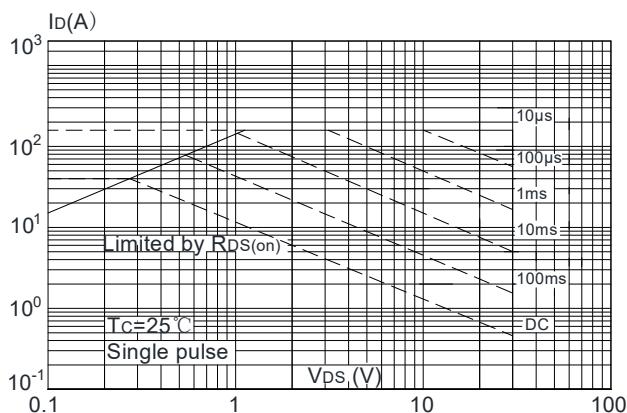


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

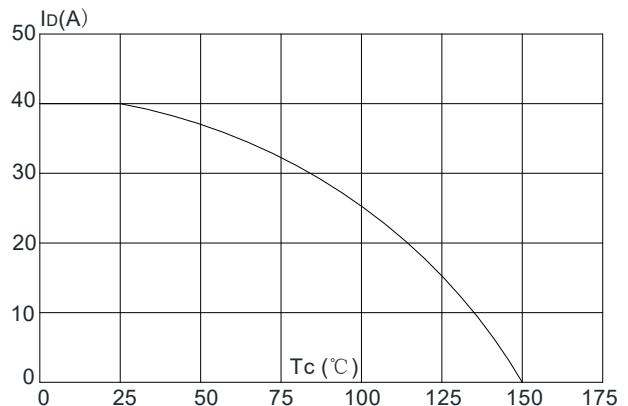
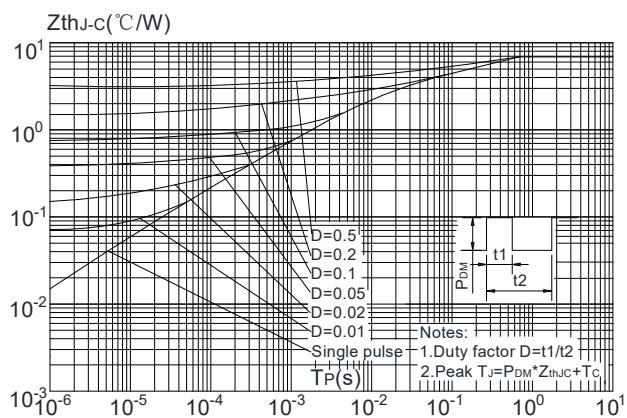


Figure 11: Maximum Effective Transient Thermal Impedance, Junction-to-Case



Test Circuit



Figure 1: Gate Charge Test Circuit & Waveform



Figure 2: Resistive Switching Test Circuit & Waveforms

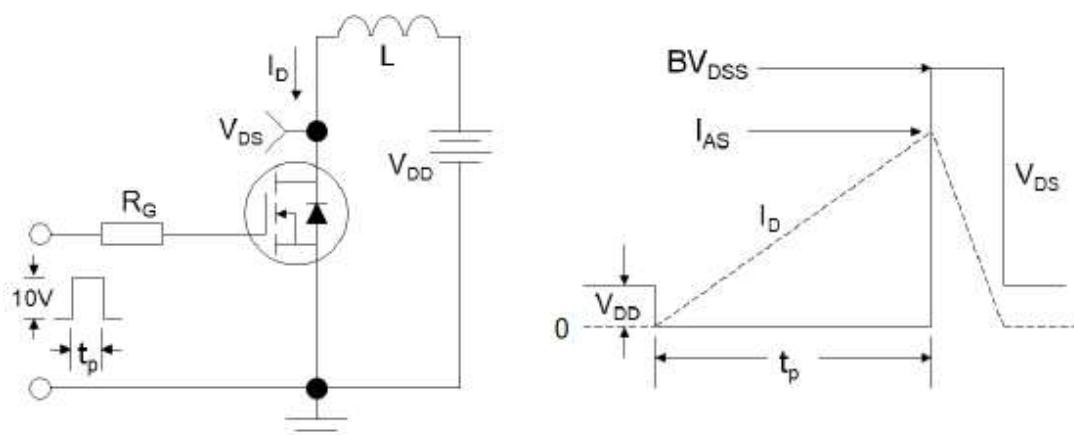
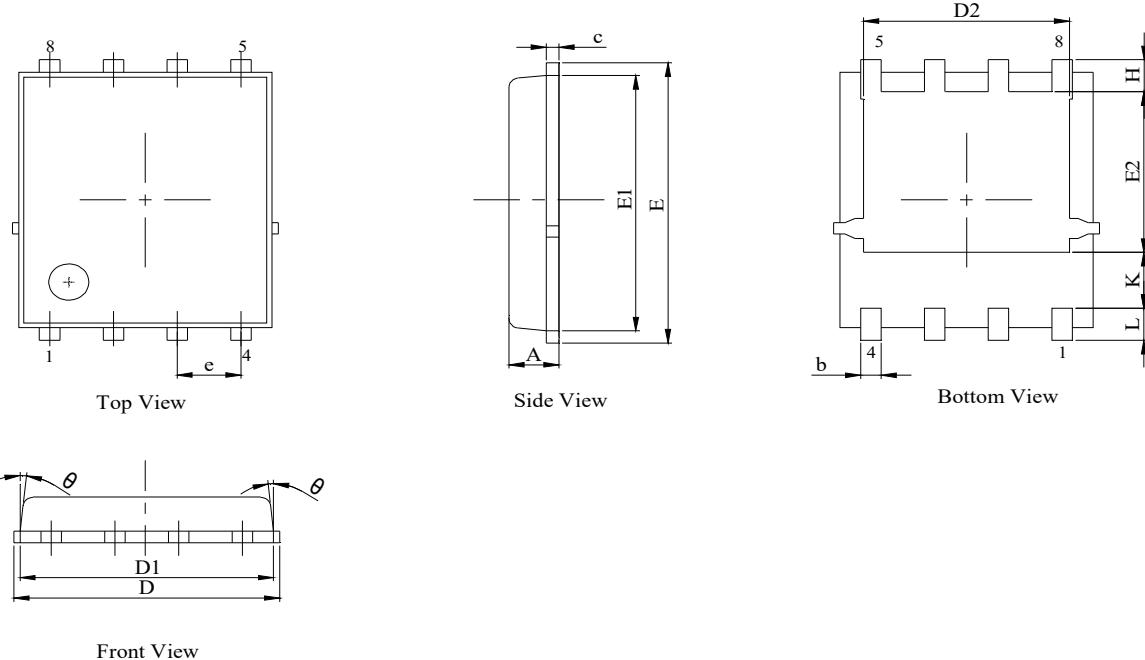


Figure 3: Unclamped Inductive Switching Test Circuit & Waveforms

PDFN5X6-8L Package Information (unit:mm)


DIM.	MILLIMETER		
	MIN.	NOM.	MAX.
A	0.90	1.00	1.10
b	0.31	0.41	0.51
c	0.20	0.25	0.30
D	5.00	5.20	5.40
D1	4.95	5.05	5.15
D2	4.00	4.10	4.20
E	6.05	6.15	6.25
E1	5.50	5.60	5.70
E2	3.42	3.53	3.63
e	1.27BSC		
H	0.60	0.70	0.80
L	0.50	0.70	0.80
θ	-	-	10°